

# N-Channel Reduced $Q_g$ , Fast Switching MOSFET

## PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ )  | $I_D$ (A) | $Q_g$ (Typ.) |
|--------------|----------------------------|-----------|--------------|
| 30           | 0.007 at $V_{GS} = 10$ V   | 16        | 11           |
|              | 0.0095 at $V_{GS} = 4.5$ V | 13.5      |              |

## FEATURES

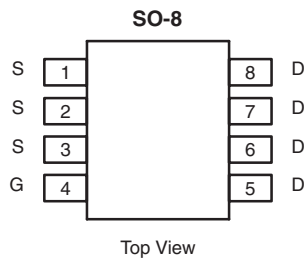
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Gen II Power MOSFETs
- PWM Optimized
- 100 %  $R_g$  Tested



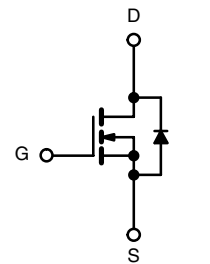
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

## APPLICATIONS

- DC/DC Conversion for PC



**Ordering Information:** Si4386DY-T1-E3 (Lead (Pb)-free)  
Si4386DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter                                                 | Symbol         | 10 s        | Steady State | Unit |
|-----------------------------------------------------------|----------------|-------------|--------------|------|
| Drain-Source Voltage                                      | $V_{DS}$       | 30          |              | V    |
| Gate-Source Voltage                                       | $V_{GS}$       | $\pm 20$    |              |      |
| Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>   | $I_D$          | 16          | 11           | A    |
|                                                           |                | 13          | 9            |      |
| Pulsed Drain Current                                      | $I_{DM}$       | $\pm 50$    |              |      |
| Continuous Source Current (Diode Conduction) <sup>a</sup> | $I_S$          | 2.8         | 1.3          |      |
| Single Pulse Avalanche Current                            | $I_{AS}$       | 20          |              | mJ   |
| Avalanche Energy                                          | $E_{AS}$       | 20          |              |      |
| Maximum Power Dissipation <sup>a</sup>                    | $P_D$          | 3.1         | 1.47         | W    |
|                                                           |                | 2           | 0.95         |      |
| Operating Junction and Storage Temperature Range          | $T_J, T_{stg}$ | - 55 to 150 |              | °C   |

## THERMAL RESISTANCE RATINGS

| Parameter                                         | Symbol     | Typical | Maximum | Unit |
|---------------------------------------------------|------------|---------|---------|------|
| Maximum Junction-to-Ambient (MOSFET) <sup>a</sup> | $R_{thJA}$ | 34      | 40      | °C/W |
|                                                   |            | 71      | 85      |      |
| Maximum Junction-to-Foot (Drain)                  | $R_{thJF}$ | 18      | 22      |      |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

| MOSFET SPECIFICATIONS $T_J = 25^\circ\text{C}$ , unless otherwise noted |              |                                                                                                                        |      |        |           |               |
|-------------------------------------------------------------------------|--------------|------------------------------------------------------------------------------------------------------------------------|------|--------|-----------|---------------|
| Parameter                                                               | Symbol       | Test Conditions                                                                                                        | Min. | Typ.   | Max.      | Unit          |
| <b>Static</b>                                                           |              |                                                                                                                        |      |        |           |               |
| Gate Threshold Voltage                                                  | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$                                                                           | 1.5  | 2.0    | 2.5       | V             |
| Gate-Body Leakage                                                       | $I_{GSS}$    | $V_{DS} = 0\ \text{V}$ , $V_{GS} = \pm 20\ \text{V}$                                                                   |      |        | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                                         | $I_{DSS}$    | $V_{DS} = 30\ \text{V}$ , $V_{GS} = 0\ \text{V}$                                                                       |      |        | 1         | $\mu\text{A}$ |
|                                                                         |              | $V_{DS} = 30\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $T_J = 70^\circ\text{C}$                                            |      |        | 10        |               |
| On-State Drain Current <sup>a</sup>                                     | $I_{D(on)}$  | $V_{DS} \geq 5\ \text{V}$ , $V_{GS} = 10\ \text{V}$                                                                    | 40   |        |           | A             |
| Drain-Source On-State Resistance <sup>a</sup>                           | $R_{DS(on)}$ | $V_{GS} = 10\ \text{V}$ , $I_D = 16\ \text{A}$                                                                         |      | 0.0058 | 0.007     | $\Omega$      |
|                                                                         |              | $V_{GS} = 4.5\ \text{V}$ , $I_D = 13.5\ \text{A}$                                                                      |      | 0.0078 | 0.0095    |               |
| Forward Transconductance <sup>a</sup>                                   | $g_{fs}$     | $V_{DS} = 15\ \text{V}$ , $I_D = 16\ \text{A}$                                                                         |      | 51     |           | S             |
| Diode Forward Voltage <sup>a</sup>                                      | $V_{SD}$     | $I_S = 2.8\ \text{A}$ , $V_{GS} = 0\ \text{V}$                                                                         |      | 0.75   | 1.1       | V             |
| <b>Dynamic<sup>b</sup></b>                                              |              |                                                                                                                        |      |        |           |               |
| Total Gate Charge                                                       | $Q_g$        | $V_{DS} = 15\ \text{V}$ , $V_{GS} = 4.5\ \text{V}$ , $I_D = 16\ \text{A}$                                              |      | 11     | 18        | nC            |
| Gate-Source Charge                                                      | $Q_{gs}$     |                                                                                                                        |      | 5.8    |           |               |
| Gate-Drain Charge                                                       | $Q_{gd}$     |                                                                                                                        |      | 3.0    |           |               |
| Gate Resistance                                                         | $R_g$        |                                                                                                                        | 0.8  | 1.7    | 2.5       | $\Omega$      |
| Turn-On Delay Time                                                      | $t_{d(on)}$  | $V_{DD} = 15\ \text{V}$ , $R_L = 15\ \Omega$<br>$I_D \cong 1\ \text{A}$ , $V_{GEN} = 10\ \text{V}$ , $R_g = 6\ \Omega$ |      | 12     | 18        | ns            |
| Rise Time                                                               | $t_r$        |                                                                                                                        |      | 9      | 14        |               |
| Turn-Off Delay Time                                                     | $t_{d(off)}$ |                                                                                                                        |      | 35     | 53        |               |
| Fall Time                                                               | $t_f$        |                                                                                                                        |      | 10     | 15        |               |
| Source-Drain Reverse Recovery Time                                      | $t_{rr}$     | $I_F = 2.8\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$                                                            |      | 25     | 50        |               |

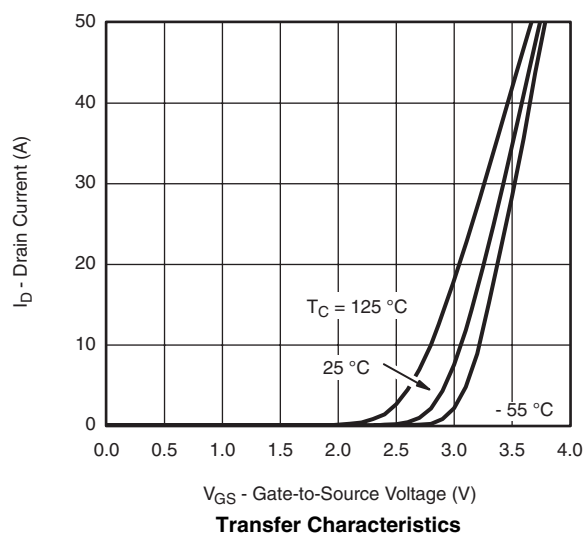
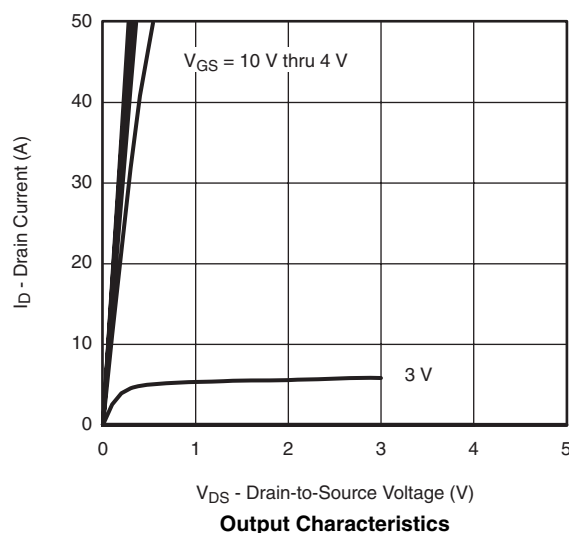
Notes:

a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

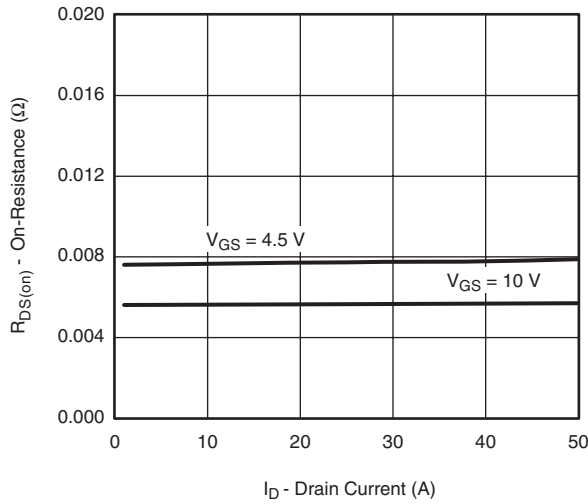
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

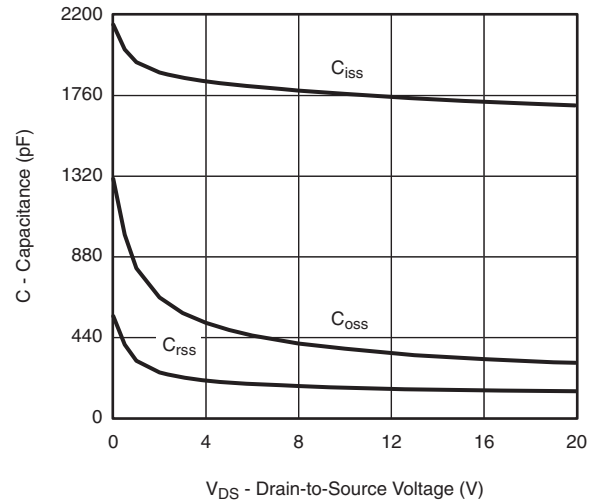
## TYPICAL CHARACTERISTICS $25^\circ\text{C}$ , unless otherwise noted



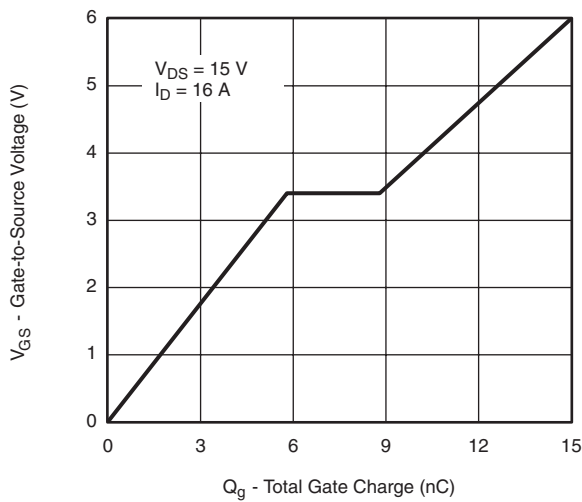
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



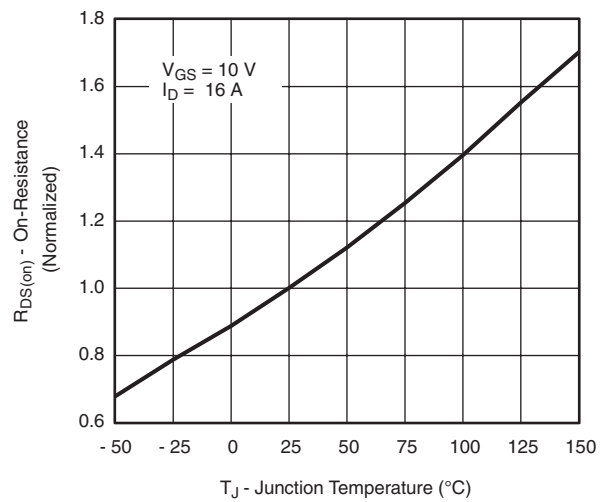
**On-Resistance vs. Drain Current**



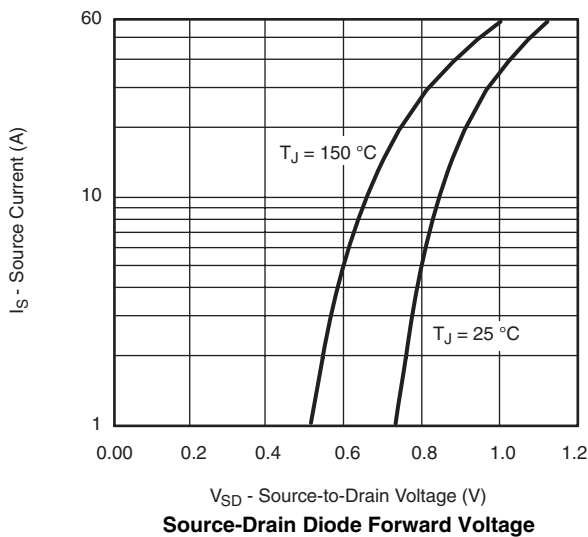
**Capacitance**



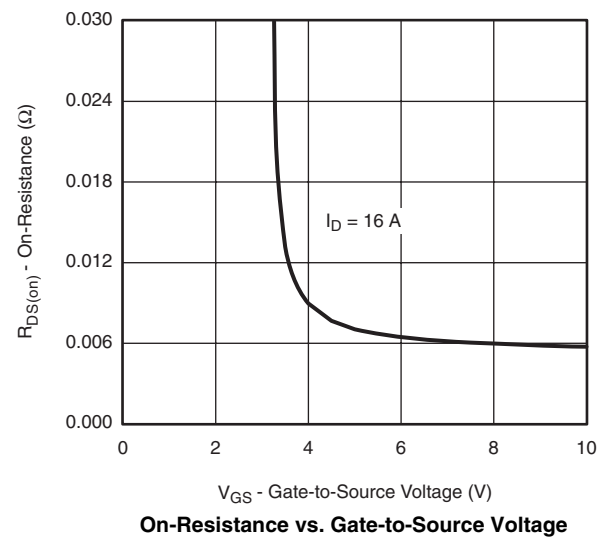
**Gate Charge**



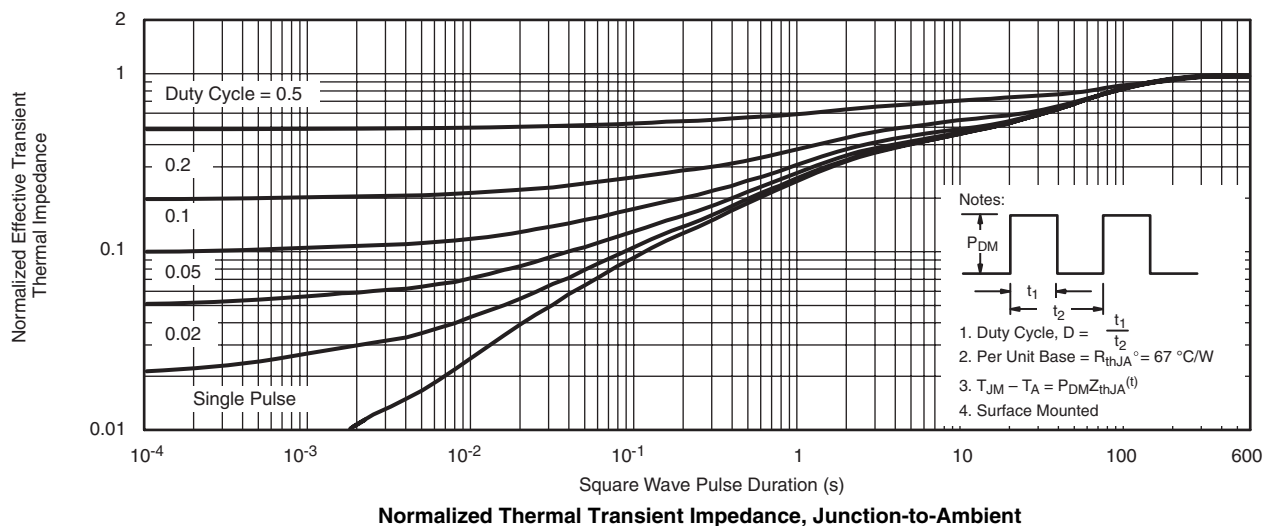
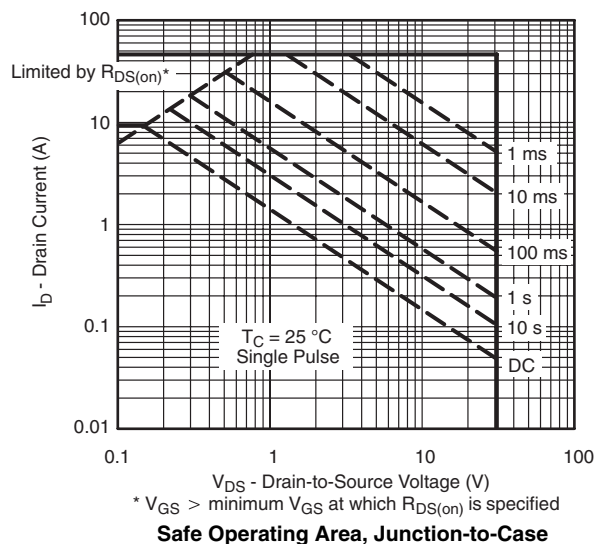
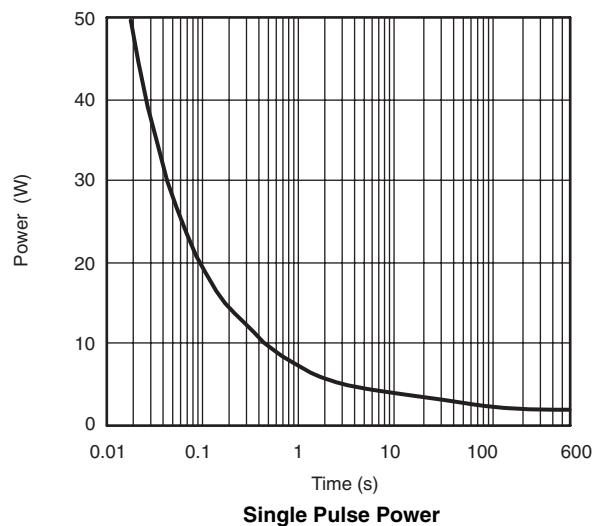
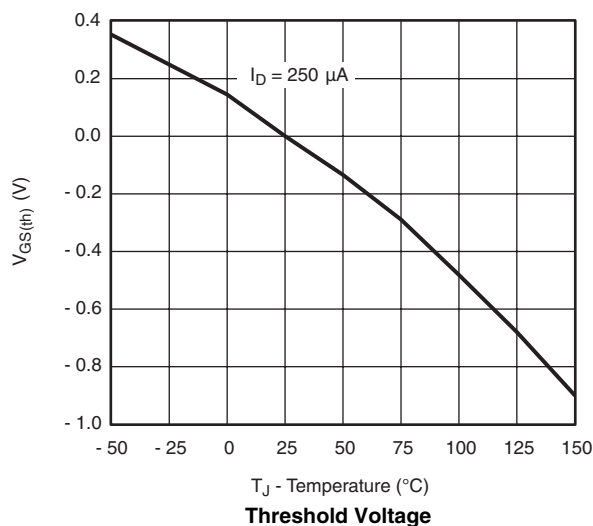
**On-Resistance vs. Junction Temperature**



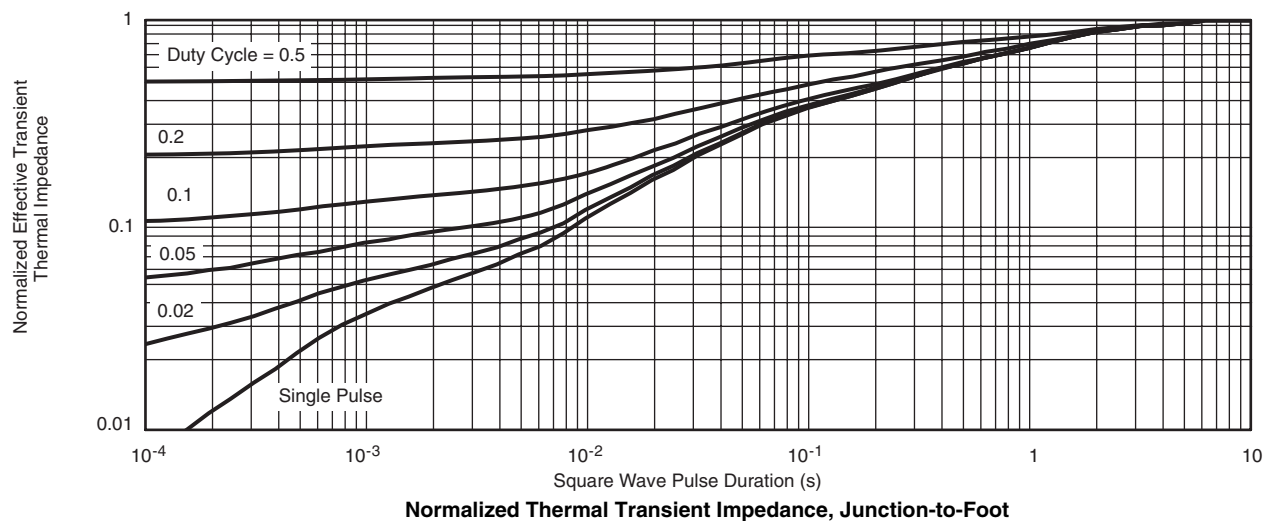
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

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## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



| DIM                            | MILLIMETERS |      | INCHES    |       |
|--------------------------------|-------------|------|-----------|-------|
|                                | Min         | Max  | Min       | Max   |
| A                              | 1.35        | 1.75 | 0.053     | 0.069 |
| A <sub>1</sub>                 | 0.10        | 0.20 | 0.004     | 0.008 |
| B                              | 0.35        | 0.51 | 0.014     | 0.020 |
| C                              | 0.19        | 0.25 | 0.0075    | 0.010 |
| D                              | 4.80        | 5.00 | 0.189     | 0.196 |
| E                              | 3.80        | 4.00 | 0.150     | 0.157 |
| e                              | 1.27 BSC    |      | 0.050 BSC |       |
| H                              | 5.80        | 6.20 | 0.228     | 0.244 |
| h                              | 0.25        | 0.50 | 0.010     | 0.020 |
| L                              | 0.50        | 0.93 | 0.020     | 0.037 |
| q                              | 0°          | 8°   | 0°        | 8°    |
| S                              | 0.44        | 0.64 | 0.018     | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 |             |      |           |       |
| DWG: 5498                      |             |      |           |       |

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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